Form PTO-1449 Sheet 1 of 2 Applicant: Ryuzo Iga et al. Confirmation No: 9935 Serial No.: 10/577,626 Att'v Docket No.: 14321.84 Filing Date: April 28, 2006 Art Unit: 2828 For: SEMICONDUCTOR OPTICAL DEVICE AND A METHOD OF FABRICATING THE SAME

INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANT

U.S. Patent Documents

Examiner	Document	Issue	
Initial*	Number	<u>Date</u>	Name
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 Sheet 2 of 2

 Applicant
 Ryuzo Iga et al.

 Sorial No.: 9035
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The reference designations "A1," "A2," etc. (referring to Applicant's reference 1, Applicant's reference 2, etc.) will be used by the Examiner in the same manner as Examiner's reference designations "A," "B," "C," etc. on Office Action Form PTO-1142.

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